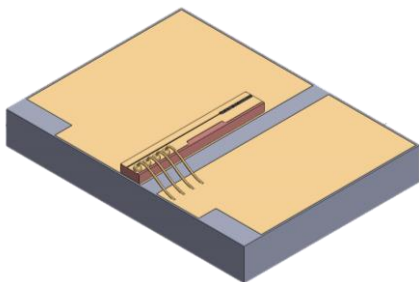
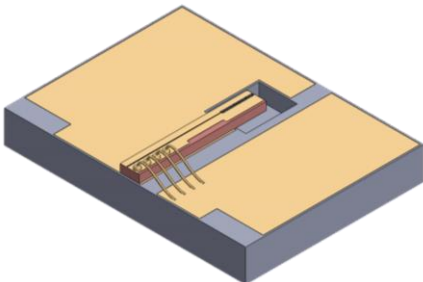


Specification Sheet | 976 nm Series
Distributed Bragg Reflector (DBR) Laser Diode



Chip on Submount (CoS)



CoS + Mode-Hop Free (MHF)

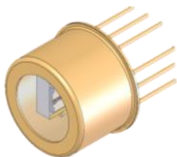
Description

976 nm DBR Chip on Submount (CoS) Characteristics

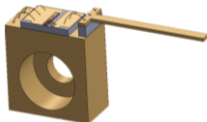
| Parameters ¹ | Chip Architecture |
|---|-------------------|
| | High Power |
| Wavelength, Nominal (nm) ² | 976 |
| Power Range (mW) | 80–350 |
| Operating Current, Max (CW & Pulsed) (mA) | 400 |
| Optical Power at Max Operating Current (mW) | / |
| Slope Efficiency, Nominal (W/A) | / |
| Threshold Current, Nominal (mA) | / |

1. Characteristics at $T_c = 25^\circ\text{C}$ unless otherwise specified. Operating outside of these parameters voids warranty.
2. Hermetically sealed packages may contain CoS that are $\pm 1.2\text{ nm}$ from nominal

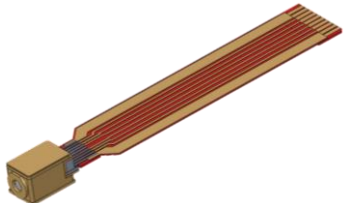
Available Free-Space Package Add-ons



TO-8



C-Mount



Transmitter Optical Subassembly (TOSA)

Specification Sheet | 976 nm Series

Distributed Bragg Reflector (DBR) Laser Diode

Specifications

Laser

| Parameter | Unit | Min | Typical | Max |
|---|------------------|-----|---------|--------|
| Storage Temperature | °C | 0 | - | 70 |
| Operating Temperature at case | °C | 5 | - | 70 |
| Operating Temperature at laser chip ¹ | °C | 5 | - | 45 |
| Laser Series Resistance | Ω | - | 2 | - |
| Laser Forward Voltage @ LIV Current | V | - | 2 | - |
| Nominal Laser Linewidth @ LIV Current | kHz | - | 500 | - |
| Beam Divergence @ FWHM ($\theta_{ }$ x θ_{\perp}) | ° | - | 6 x 28 | 8 x 32 |
| Side Mode Suppression Ratio (SMSR) | dB | - | -40 | - |
| Polarization Extinction Ratio | dB | -17 | -20 | - |
| Laser Polarization | TE | | | |
| Mode Structure | Fundamental Mode | | | |
| Temperature Tuning Rate | nm/°C | - | 0.06 | - |
| Current Tuning Rate | nm/mA | - | 0.002 | - |
| Laser Reverse Voltage | V | - | - | 0 |

1. Operation below dew point not recommended without hermetically sealed packaged

Free-Space Package Add-Ons

| Parameter | Unit | Min | Typical | Max |
|----------------------------|------|------|---------|-----|
| Photodiode Forward Current | mA | - | - | 10 |
| Photodiode Reverse Voltage | V | - | - | 50 |
| TEC Current (TOSA) | A | -1.1 | - | 1.1 |
| TEC Voltage (TOSA) | V | -3.0 | - | 3.0 |
| TEC Current (TO-8) | A | -1.8 | - | 1.8 |
| TEC Voltage (TO-8) | V | -2.2 | - | 2.2 |
| Thermistor Resistance | kΩ | - | 10 | - |

Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic container with all leads shorted together.

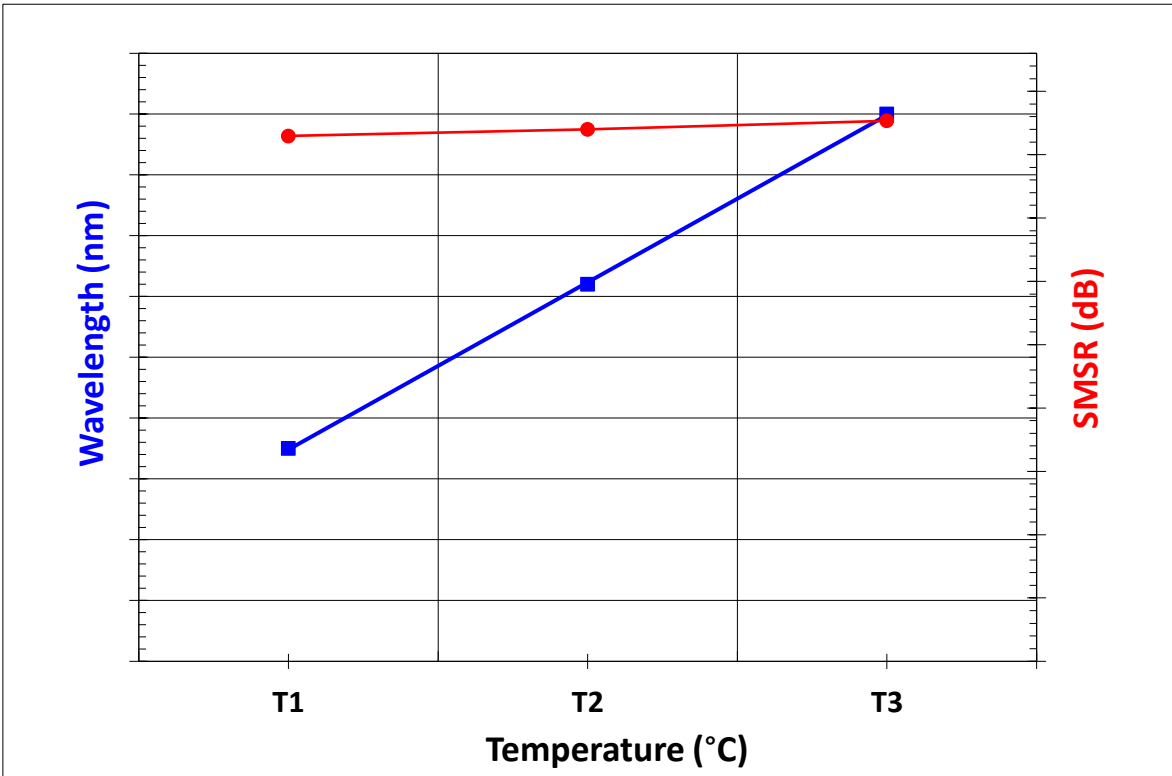


Photodigm, Inc. reserves the right to make changes in design, specifications, and other information at any time, and without prior notice. The information contained within the specification sheet is believed to be accurate. However, no responsibility is assumed for possible inaccuracy or omission. Any information contained herein shall not legally bind Photodigm, Inc. unless it is specifically incorporated in the terms and conditions of a sales agreement.

Specification Sheet | **976 nm Series**

Distributed Bragg Reflector (DBR) Laser Diode

Air Wavelength Characteristics at Constant Current by Temperature



LIV Characteristics by Current

